## NSN 5962-01-111-0435

Memory Microcircuit - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5962-01-111-0435 **Body Length:** Between 0.755 inches and 0.785 inches **Body Width:** 0.302 inches **Body Height:** Between 0.145 inches and 0.175 inches **Maximum Power Dissipation Rating:** 500.0 milliwatts **Operating Tempurature Range:** -55.0/+125.0 degrees celsius Storage Tempurature Range: -65.0/+150.0 degrees celsius **Features Provided:** Hermetically sealed and monolithic and 3-state output and w/enable and programmable **Inclosure Material:** Ceramic and glass **Inclosure Configuration:** Dual-in-line **Output Logic Form:** Transistor-transistor logic **Input Circuit Pattern:** 10 input **Terminal Surface Treatment:** Solder Voltage Rating And Type Per Characteristic: 7.0 volts power source **Time Rating Per Chacteristic:** 60.00 nanoseconds propagation delay time, low to high level output and 60.00 nanoseconds propagation delay time, high to low level output **Memory Device Type:** Rom **Test Data Document:** 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.). **Terminal Type And Quantity:** 16 printed circuit Shelf Life: N/a **Unit Of Measure:** 

No Fiig:

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**Demilitarization:**